

1765
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2/11/03
PATENT
29936/37431

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Sung Gyu Pyo

Serial No.: 09/875,698

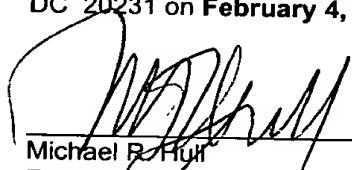
Filed: June 6, 2001

For: Method of Forming a Metal
Wiring in a Semiconductor Device

Group Art Unit: 1765

Examiner: Lynettte T. Umez
Eronini

) I hereby certify that this paper is being
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) DC 20231 on February 4, 2003


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AMENDMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the office action mailed on November 4, 2002, please enter the following amendments and remarks.

In the Specification:

Please replace the paragraph beginning on page 4, line 17, with the following rewritten paragraph:

Ac. --The chemical enhancer layer 60 is formed in thickness ranging from about 50 to about 500 Å. Materials for forming the chemical enhancer layer 60 may include one of I (iodine)-containing liquid compounds such as CH₃I, C₂H₅I, CD₃I, CH₂I₂ etc., Hhfac1/2H₂O, Hhfac, TMVS, pure I₂, I (iodine)-containing gas and water vapor, and is performed at the temperature ranging from about -20 to about 300°C for a time period ranging from about 1 to about 600 seconds. Also, the materials may include F, Cl, Br, I, At of a liquid state and F, Cl, Br, I, At of a gas state, which are Group VII elements in the Periodic Table.--